

Supporting Information

for

Isolation of cubic Si₃P₄ in the form of nanocrystals

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Additional experimental data

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Selected temperature for doping of Si NPs with phosphorus and the calculation of the diffusion constant resulted from the equation $D = D_0 e^{\frac{-Q}{RT}}$, where D₀=20 cm²/sec, Q=364 kJ/mol, T=670°C [1].





Figure S1: EDX spectra of (a),(b) – SP550, (c) – SP670.

Table S1: The correlation of bands and wavenumbers for Si NPs, hydrogenated Si NPs and SP400,

SP670 and SP900 samples.

Assignment	Wavenumber, cm ⁻¹								
	Reference data	Sample							
		Si NPs	Hydrogenated Si NPs	SP400	SP670	SP900			
O-H stretching	3700-3200	3420	3509	-	3450	3329			
	[2]		3450						
=С-Н	3100-3000	-	-	3073	-	-			
stretching	[2]								
Methyl asymmetric C- H stretching	2960 [3]	2960	2957	2956	2960	2956			
Methylene asymmetric C- H stretching	2930 [2]	2925	2924	2925	2926	2921			
Methylene symmetric C-H stretching	2850 [2]	2854	2855	2853	2857	2853			
(O ₃)Si-H stretching	2250 [4]	2267	-	-	-	2266			
(Si ₃)Si-H stretching	2100 [4]	2105	2107	-	-	-			
Overtone HRC=CH ₂	1850-1800 [3]			1821					
C=O stretching	1730 [2]	1728	1711	1743-1730- 1718	1714	1720			
H ₂ O deformation	1640 [5]	1623	1631	-	1646	1641			
C=C	1680-1600	-	-	1642	-	-			
stretching	[2]								
Methylene scissoring	1465 [2]	1465	1466	1466	1469	1465			
Methyl symmetrical C- H bending	1380 [2]	-	_	1378	-	-			

Methylene twisting	1300 [2]	-	-	1302	-	-
Si-O-Si stretching	1200-1000	1208	1167	1186	1205	1183
	[2], [6]	1069	1072	1098	1090	1073
C-H	995-985	-	-	992	-	-
deformation non-planar (vinyl)	[3]					
С-Н	915-905	-	-	911	-	-
deformation non-planar (vinyl)	[3]					
H-Si-O ₃	880	880	-	-	-	874
deformation	[6]					
H-Si-O ₂	850	-	863	-	-	-
deformation	[6]					
Si-O-Si symmetrical stretching	810	804	814	806	801	806
	[7]					
Methylene rocking	720	-	720	721	-	_
	[2]					
=C-H out-of- plane bending	1000-600	-	-	668	-	-
	[2]					
Si-Si-H _x	637	633	-	-	-	-
deformation	[6]					
Si-P	-	-	-	494	492	490
stretching						
Si-O-Si	450	452	-	-	-	-
rocking	[7]					

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